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Title: THIN FILM DEPOSITION METHODS AND APPARATUSES

Amendments to the Specification

Please replace the paragraph beginning on page 18, line 18 with the following amended paragraph:

Wafer 46 is further illustrated in Figure 3. As shown, wafer 46 includes first cavity 50 and second cavity 52. (Alternatively, according to the invention fewer or more, or no cavities may be included in a substrate.) First cavity 50 includes base surface 54, and second cavity 52 includes base surface 56. Wafer 46 may be formed from any desired material such as silicon, Pyrex, quartz, etc. First cavity 50 and second cavity 52 may have any desired shape, ~~shape,~~ and depth. For example, wafer 46 may be silicon. First cavity 50 or second cavity 52 can be cylindrical cavities that have a diameter of 0.5 to 2 mm and a depth of 0 to 1000 microns, e.g., a depth of 10 to 200 microns, for example. First and second cavities 50 and 52 may have the same or similar sizes and shapes or may have different sizes and shapes as well as depth. For example, as shown, second cavity 52 is larger than the first cavity 50. Preferably, such cavity structures are suitable for cell type atomic clock structures.